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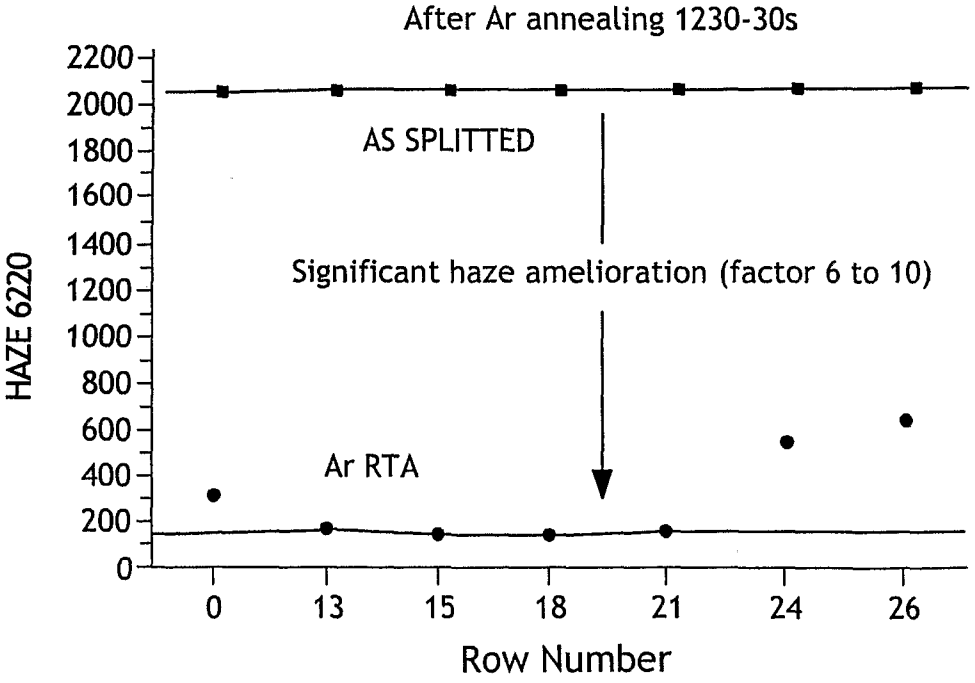
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(54) Title: PROCESS FOR IMPROVING THE SURFACE ROUGHNESS OF A SEMICONDUCTOR WAFER



(57) Abstract: The present invention relates to a process for reducing the roughness of the free surface of a semiconductor wafer, said process comprising a single annealing step for smoothing said free surface, said single annealing step being carried out as a RTA under an atmosphere of pure argon, characterized in that before the RTA a chemical cleaning of the wafer surface is carried out so as to reduce the amount of preliminary pollutants on the wafer.

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